

# Tian Shen

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/11974335/publications.pdf>

Version: 2024-02-01

11

papers

344

citations

1478505

6

h-index

1588992

8

g-index

11

all docs

11

docs citations

11

times ranked

750

citing authors

#	ARTICLE	IF	CITATIONS
1	Charge transport model to predict dielectric breakdown as a function of voltage, temperature, and thickness. <i>Microelectronics Reliability</i> , 2018, 91, 232-242.	1.7	3
2	Method to Determine the Root Cause of Low- $\kappa$ SiCOH Dielectric Failure Distributions. <i>IEEE Electron Device Letters</i> , 2017, 38, 119-122.	3.9	1
3	A Realistic Method for Time-Dependent Dielectric Breakdown Reliability Analysis for Advanced Technology Node. <i>IEEE Transactions on Electron Devices</i> , 2016, 63, 755-759.	3.0	12
4	Impact of electrode surface modulation on time-dependent dielectric breakdown. , 2015, , .		1
5	Topological insulator based spin valve devices: Evidence for spin polarized transport of spin-momentum-locked topological surface states. <i>Solid State Communications</i> , 2014, 191, 1-5.	1.9	59
6	SYNTHETIC GRAPHENE GROWN BY CHEMICAL VAPOR DEPOSITION ON COPPER FOILS. <i>International Journal of Modern Physics B</i> , 2013, 27, 1341002.	2.0	30
7	Characteristics of graphene for quantized hall effect measurements. , 2012, , .		2
8	Quantized Hall Effect and Shubnikovâ€“de Haas Oscillations in Highly Doped $\text{Bi}_{2\text{Se}_3}$ . Evidence for Layered Transport of Bulk Carriers. <i>Physical Review Letters</i> , 2012, 108, 216803.		
9	Quantum Hall effect on centimeter scale chemical vapor deposited graphene films. <i>Applied Physics Letters</i> , 2011, 99, 232110.	3.3	33
10	Pronounced quantum hall-effect on epitaxial graphene up to 70K. , 2009, , .		0
11	Substrate engineering for high-performance surface-channel III-V metal-oxide-semiconductor field-effect transistors. <i>Applied Physics Letters</i> , 2007, 91, .	3.3	53